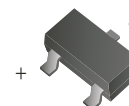


CDST19-G/20-G

High Speed
RoHS Device



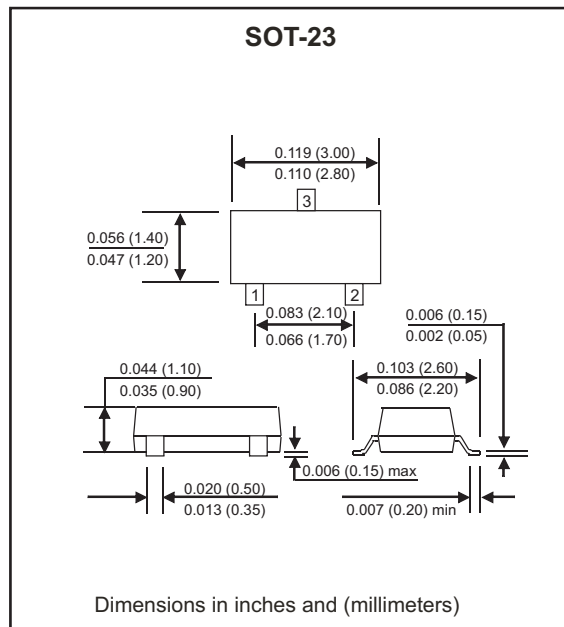
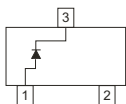
Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

- Case: SOT-23
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
- Weight: 0.008 gram.
- Marking: CDST19-G JP
CDST20-G JR

Circuit Diagram



Maximum Rating (at Ta=25°C unless otherwise noted)

Parameter	Symbol	CDST19-G	CDST20-G	Unit
Non-Repetitive peak reverse voltage	V_{RM}	100	150	V
DC blocking voltage	V_R	100	150	V
Average rectified output current	I_o	200		mA
Power dissipation	P_D	250		mW
Thermal resistance-Junction to ambient air	$R_{\theta JA}$	500		°C/W
Junction temperature	T_J	150		°C
Storage temperature range	T_{STG}	-65 ~ +150		°C

Electrical Characteristics (at TA=25 °C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V_{BR}	$I_R=100\mu A$	100 150		V
Reverse leakage current	I_R	$V_R=100V$ $V_R=150V$		0.1	UA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1 1.25	V
Junction capacitance	C_J	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=30mA, I_{rr}=0.1 \times I_R$		50	nS

Characteristic Curves (CDST19-G/20-G)

Fig.1 - Forward Characteristics

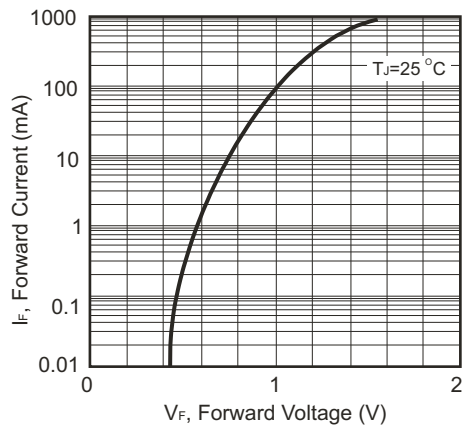
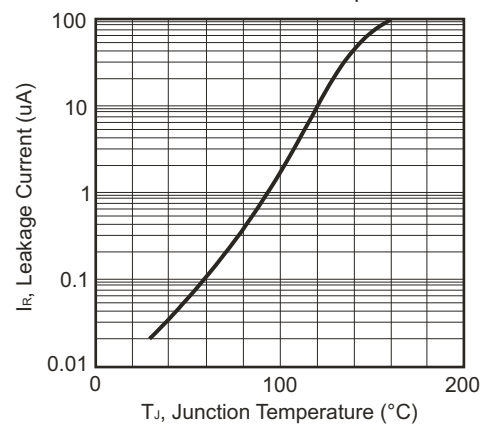


Fig.2 - Leakage Current vs Junction Temperature



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